Optically Coupled Isolator

OPI120, OPI123



Features:

- 15 kV dc electrical isolation
- Choice of phototransistor or photodarlington output
- Hermetically sealed LED and photosensor
- Base contact for conventional transistor biasing (OPI120 only)
- UL recognized File No. E58730
- Wide operating temperature range

Description:



Each Optoisolator in this data sheet contains an infrared Light Emitting Diode (LED) and a NPN silicon Photosensor. The **OPI120** has an 890 nm Light Emitting Diode (LED) and NPN phototransistor sensor, whereas the **OPI123** has a 890 nm LED and a photodarlington sensor. The devices are sealed in a precast opaque housing with a optically transmissive path between the LED and the photosensor.

The Optoisolators in this data sheet are UL recognized under UL file E58730.

This series is designed for transmission of information between one power supply voltage to another where the potentials during surge conditions are not greater than the guaranteed isolation voltage.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- High voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment

Ordering Information										
Part Number	LED Peak Wavelength	Sensor	Isolation Voltage (,000)	CTR Min	I _F (mA) Typ / Max	V _{CE} (Volts) Max	Lead Length / Spacing			
OPI120	890 nm	Transistor	45	20	10/50	25	0.40" / 0.75"			
OPI123	or 935 nm	Darlington	15	50	10 / 50	20				



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature	-55° C to +125° C
Operating Temperature	-55° C to +100° C
Input-to-Output Isolation Voltage ⁽¹⁾	± 15 kVDC
Lead Soldering Temperature (1/16" (1.6 mm) from case for 5 seconds with soldering iron) ⁽²⁾	260° C
Input Diode	
Forward DC Current ⁽³⁾	150 mA
Reverse DC Voltage	3 V
Power Dissipation ⁽⁴⁾	200 mW
Output Photosensor	
Collector-Emitter Voltage	
OPI120	25 V
OPI123	20 V
Emitter-Collector Voltage	5 V
Collector-Base Voltage	
OPI120	25 V
Power Dissipation ⁽⁵⁾	250 mW

Notes:

(1) Measured with input and output leads shorted in air with a maximum relative humidity of 50 %. UL recognition is for 15 kV dc for one minute.

(2) RMA flux is recommended. The duration can be extended to 10 seconds maximum when flow soldering.

(3) Derate linearly 2.0 mA/°C above 25° C.

(4) Derate linearly 2.67 mW/°C above 25° C.

(5) Derate linearly 3.33 mW/°C above 25° C.



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Electrical Characteristics (-40° C to +85° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS			
Input Diode									
V _F	Forward Voltage OPI120 OPI123		- -	1.5 1.5	v	I _F = 30 mA I _F = 10 mA			
I _R	Reverse Current		-	100	μA	V _R = 3 V			
Output Pho	otosensor (See OP236 for additional informa	tion - for ı	eferenc	e only)					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage OPI120 OPI123		-		v	I _c = 1 mA I _c = 1 mA			
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	I _E = 100 μA			
V _{(BR)CBO}	Collector-Base Breakdown Voltage OPI120		-	-	v	I _c = 1 mA			
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 10 V			
Coupled (Se	ee OP804 and OP805 for additional informat	ion - for re	eference	e only)					
I _{C/} I _F	DC Current Transfer Ratio OPI120 OPI123	20 50	70 -		%	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_F = 10 \text{ mA}, V_{CE} = 2 \text{ V}$			
V _{CE(SAT)}	Collector Saturation Voltage OPI120 OPI123	-	-	0.5 1.2	v	$I_F = 30 \text{ mA}, I_C = 1 \text{ mA}$ $I_F = 5 \text{ mA}, I_C = 1 \text{ mA}$			
I _{C(ON)}	On Collector Current OPI120 OP123	2.0 5.0	-	50 -	mA	I _F = 10 mA, V _{CE} = 5 V I _F = 10 mA, V _{CE} = 2 V			
I _{CB(ON)}	On Collector Base Current—OPI120	15	-	-	μΑ	I _F = 30 mA, V _{CB} = 5 V			
V _{ISO}	Isolation Voltage ⁽¹⁾	15	-	-	kV	See note 1			
t _r , t _f	Output Rise Time, Output Fall Time OPI120 OPI123		2 40		μs	See Test Circuit			

Notes:

(1) Measured with input and output leads shorted in air with a maximum relative humidity of 50 %.



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